

What is claimed is:

1. A wafer back surface treating method in which a ground or polished surface of a semiconductor wafer activated in a grinding or polishing step, with semiconductor circuits formed thereon, is deactivated.

2. A wafer back surface treating method in which a ground or polished surface of a semiconductor wafer activated in a grinding or polishing step, with semiconductor circuits formed thereon, is deactivated, wherein the deactivation treatment is implemented with an oxidizing agent.

3. A wafer back surface treating method in which a ground or polished surface of a semiconductor wafer activated in a grinding or polishing step, with semiconductor circuits formed thereon, is deactivated, wherein the deactivation treatment is implemented with blowing of ozone to the ground or polished surface thereof.

4. A wafer back surface treating method in which a ground or polished surface of a semiconductor wafer activated in a grinding or polishing step, with semiconductor circuits formed thereon, is deactivated, wherein the deactivation treatment is implemented with ozone water.

5. A wafer back surface treating method in which a ground or polished surface of a semiconductor wafer activated in a grinding or polishing step, with semiconductor circuits formed thereon, is deactivated, wherein the deactivation treatment is

implemented with illumination of the ground or polished surface thereof with ultraviolet.

6. A wafer back surface treating method in which a ground or polished surface of a semiconductor wafer activated in a grinding or polishing step, with semiconductor circuits formed thereon, is deactivated, and then a dicing sheet is adhered to the ground or polished surface of the wafer after the deactivation treatment.

7. A wafer back surface treating method in which a ground or polished surface of a semiconductor wafer activated in a grinding or polishing step, with semiconductor circuits formed thereon, is deactivated, wherein the deactivation treatment is implemented with an oxidizing agent, and then a dicing sheet is adhered to the ground or polished surface of the wafer after the deactivation treatment.

8. A wafer back surface treating method in which a ground or polished surface of a semiconductor wafer activated in a grinding or polishing step, with semiconductor circuits formed thereon, is deactivated, wherein the deactivation treatment is implemented with blowing of ozone to the ground or polished surface thereof, and then a dicing sheet is adhered to the ground or polished surface of the wafer after the deactivation treatment.

9. A wafer back surface treating method in which a ground or polished surface of a semiconductor wafer activated in a grinding or polishing step, with semiconductor circuits formed

thereon, is deactivated, wherein the deactivation treatment is implemented with ozone water, and then a dicing sheet is adhered to the ground or polished surface of the wafer after the deactivation treatment.

5 **10. A wafer back surface treating method in which a ground or polished surface of a semiconductor wafer activated in a grinding or polishing step, with semiconductor circuits formed thereon, is deactivated, wherein the deactivation treatment is implemented with illumination of the ground or polished surface thereof with ultraviolet, and then a dicing sheet is adhered to the ground or polished surface of the wafer after the deactivation treatment.**

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11. **A dicing sheet adhering apparatus having a mechanism to blow ozone to a ground or polished surface of a wafer.**

15 **12. A dicing sheet adhering apparatus having a UV illumination mechanism illuminating a UV-setting protective tape on a ground or polished surface of a wafer with ultraviolet and in addition, a mechanism to blow exhaust having cooled a UV lamp to the ground or polished surface of a wafer.**